

SEMICONDUCTOR LIGHT-RECEIVING DEVICE
ABSTRACT OF THE DISCLOSURE

A semiconductor light-receiving device includes a plurality of first conductive type second semiconductor layers formed on a first surface of a first conductive type semiconductor substrate apart from each other. Each of the first conductive type second semiconductor layers is surrounded by a second conductive type third semiconductor layer with a first semiconductor layer therebetween. The first semiconductor layer has a lower impurity concentration than the second semiconductor layers. By completely depleting the first semiconductor layer occupying a large area within the light-receiving surface, the light entering the light-receiving surface is enabled to contribute to a photoelectric current while reducing the light absorption in the second semiconductor layers, so that the sensitivity characteristics of the semiconductor light-receiving device can be made superior and the production cost can be lowered.

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